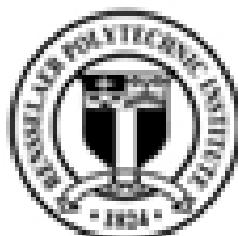


Beyond graphene: The amazing world of layered transition metal dichalcogenides (TMDs)

Humberto Terrones

Department of Physics, Applied Physics and Astronomy



Rensselaer

Layered Materials (1959)

What could we do with layered structures with just the right layers? What would the properties of materials be if we could really arrange the atoms the way we want them... I can hardly doubt that when we have some control of the arrangement of things on a small scale, we will get an enormously greater range of possible properties that substances can have...

R. P. Feynman

There is Plenty of Room at the Bottom

December 29, 1959



Structure of monolayer TMDs

Transition metal dichalcogenides exhibit two main phases:

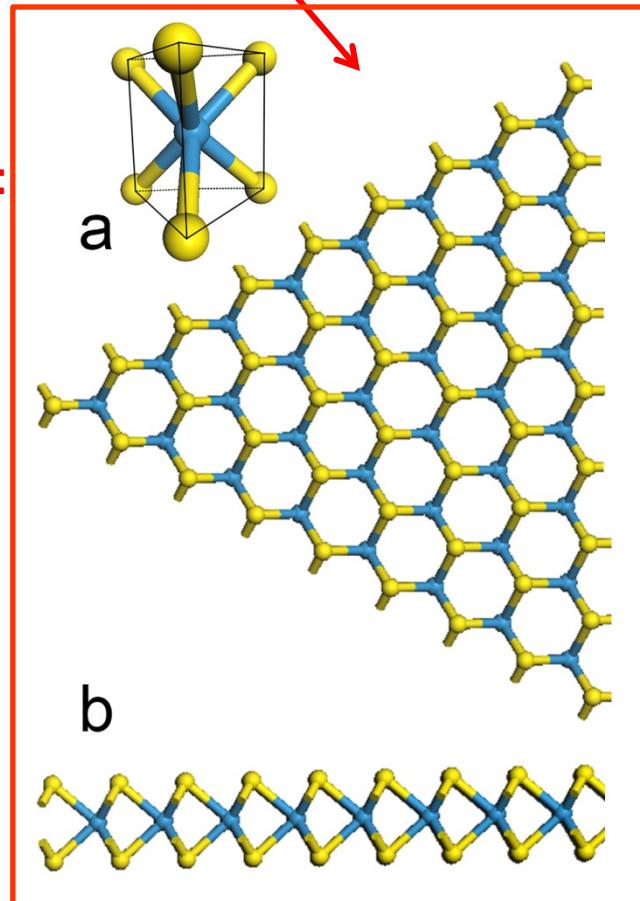
*Trigonal prismatic (Hexagonal)
(P6₃/mmc)

Semiconductor:

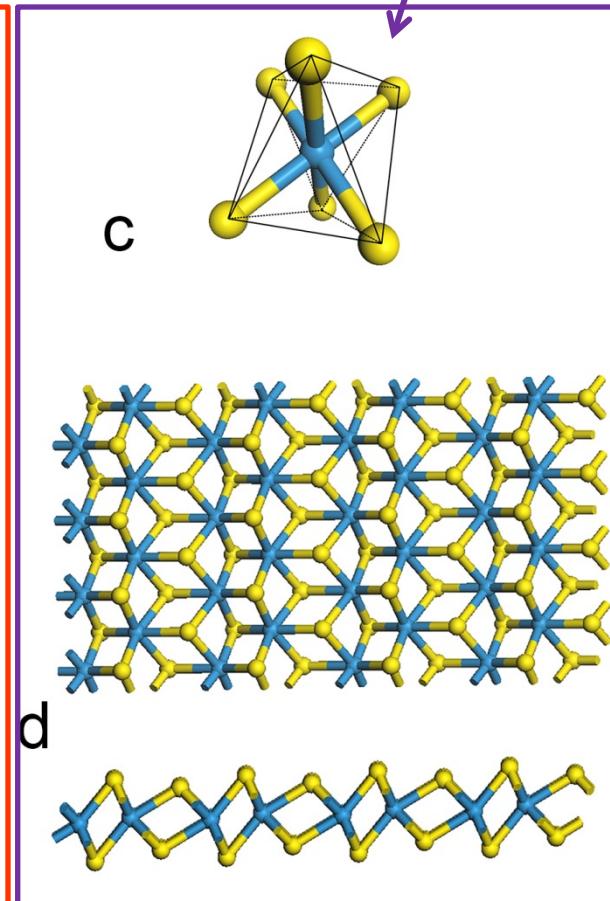
MoS₂, WS₂,
MoSe₂, WSe₂

Metal:

NbS₂, NbSe₂



*Octahedral (P2₁/m)

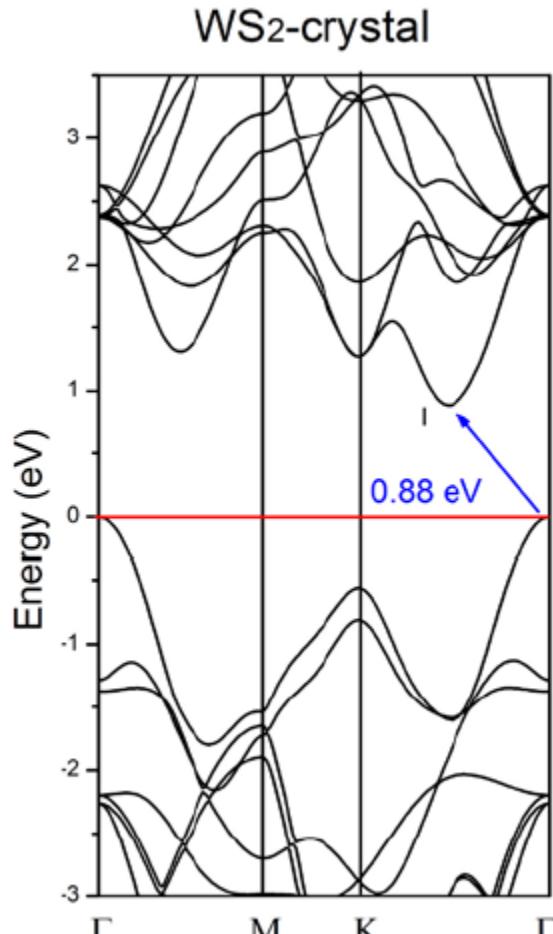


Metal:

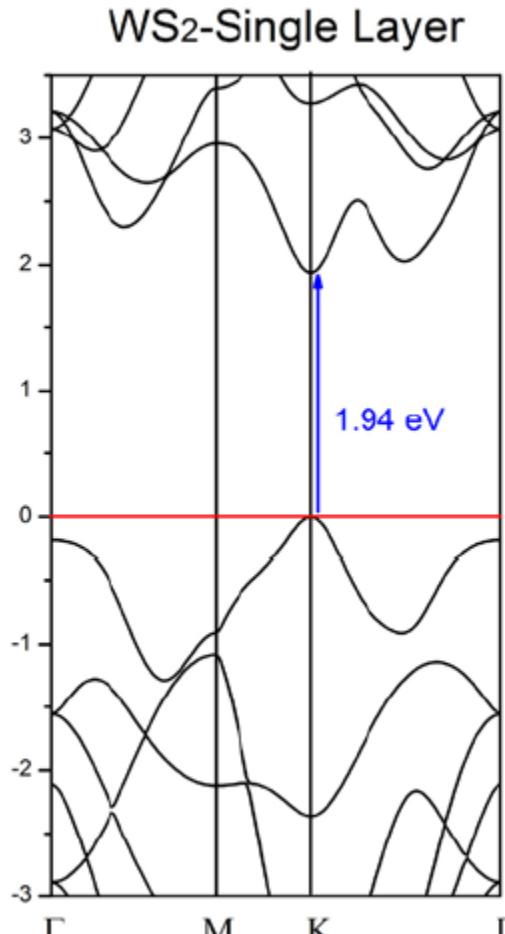
MoS₂,
WS₂,
MoSe₂,
WSe₂

Trigonal prismatic is more stable

Multi layer and Single layer behavior

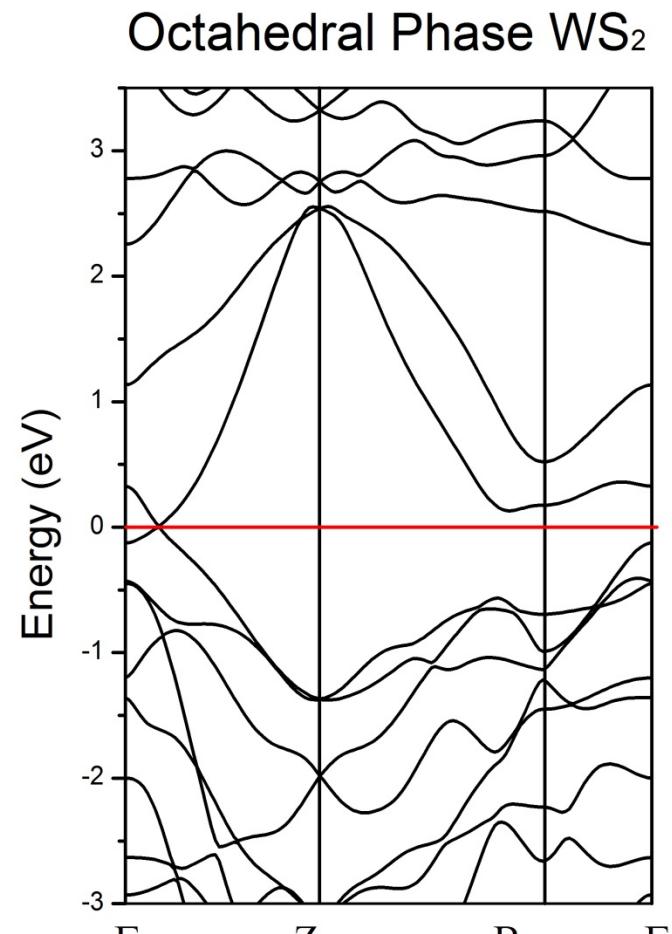


Indirect band gap



Direct band gap

Mak, K.F., et al, PRL , 105, 136805 (2010)



Metallic

Single Crystals of MoS₂ Several Molecular Layers Thick

R. F. FRINDT*

*Physics and Chemistry of Solids, Cavendish Laboratory,
Cambridge, England*

(Received 24 March 1965; in final form 18 June 1965)

[J. Appl. Phys.](#) **37**, 1928 (1966); doi: 10.1063/1.1708627

Early workers on electron diffraction prepared thin fragments of MoS₂^{2,3}; however no direct thickness measurements were made. It is now well known that small MoS₂ crystals thin enough to be transparent in the electron microscope can be prepared by the stripping technique using adhesive tape. Crystals of

The called scotch tape method for exfoliating graphite

SINGLE-LAYER MoS₂

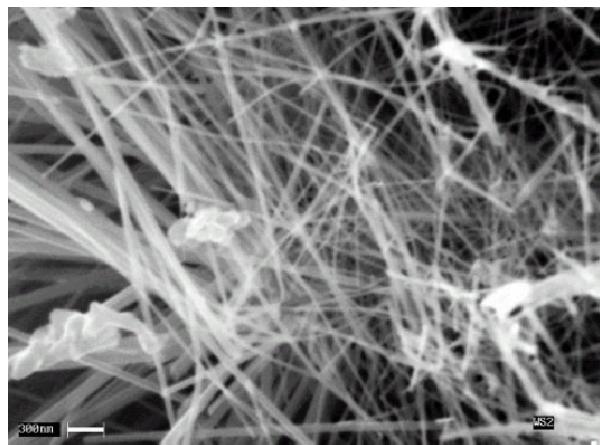
Per Joensen, R.F. Frindt, and S. Roy Morrison
Energy Research Institute
Department of Physics
Simon Fraser University
Burnaby, B.C., Canada V5A 1S6

Mat. Res. Bull., Vol. 21, pp. 457-461, 1986. Printed in the USA.

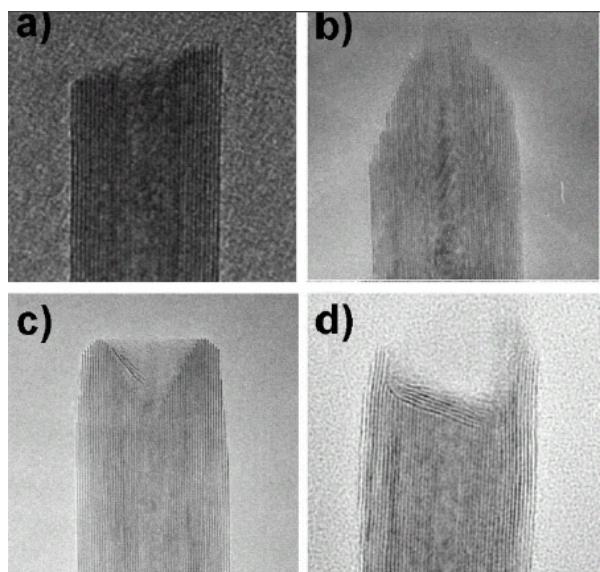
ABSTRACT

MoS₂ has been exfoliated into monolayers by intercalation with lithium followed by reaction with water. X-ray diffraction analysis has shown that the exfoliated MoS₂ in suspension is in the form of one-molecule-thick sheets. X-ray patterns from dried and re-stacked films of exfoliated MoS₂ indicate that the layers are randomly stacked. Exfoliated MoS₂ has been deposited on alumina particles in aqueous suspension, enabling recovery of dry exfoliated MoS₂ supported on alumina.

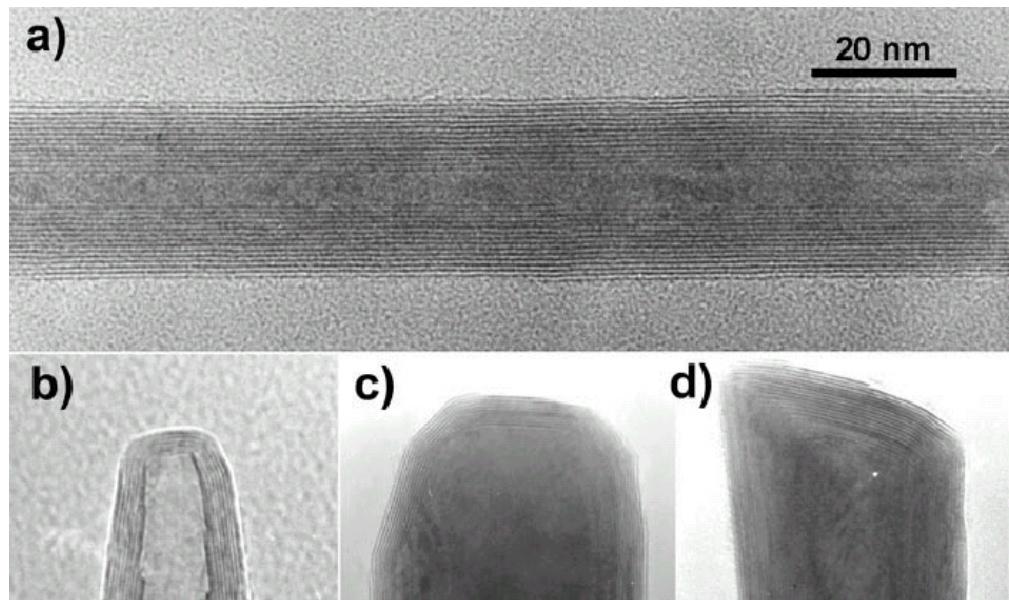
WS₂ Nanotubes: Sulfurization Process



SEM image



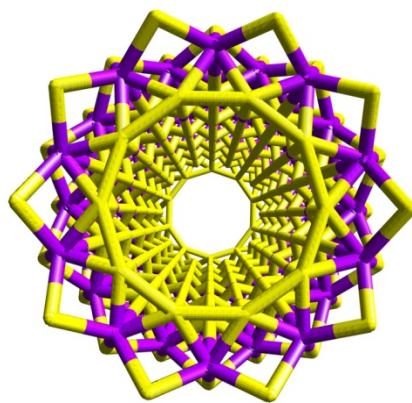
Open Nanotube Caps



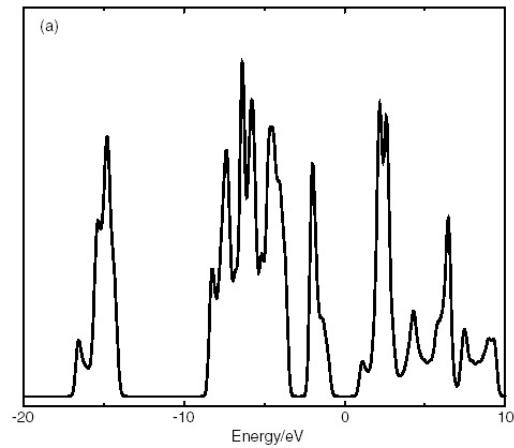
TEM images

Zhu, Y.Q., et al. *Chemistry of Materials* 12, 1190-1194 (2000);
Journal of Materials Chemistry 10, 2570-2577 (2000)

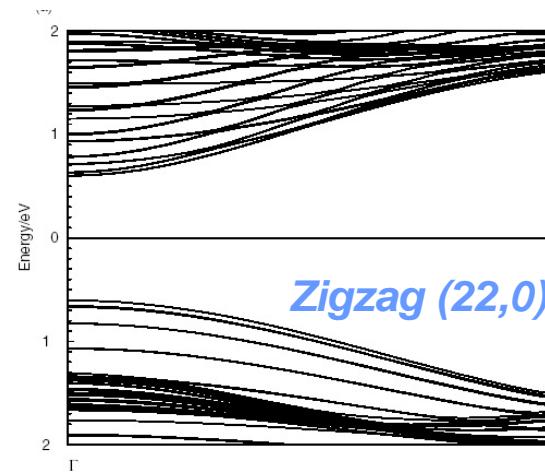
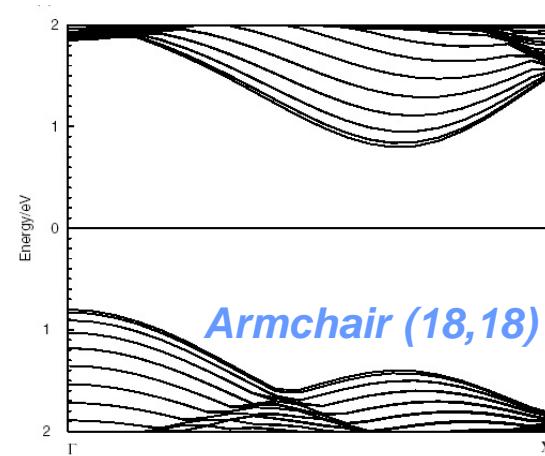
WS₂ Nanotubes: Electronic Properties



Molecular Model

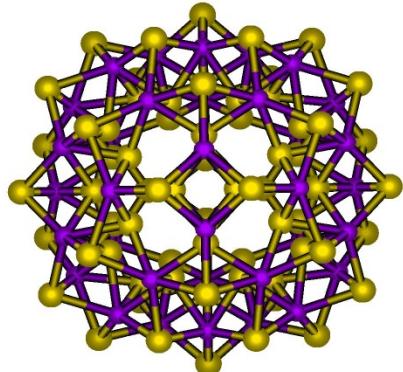


DOS for a (18,18)

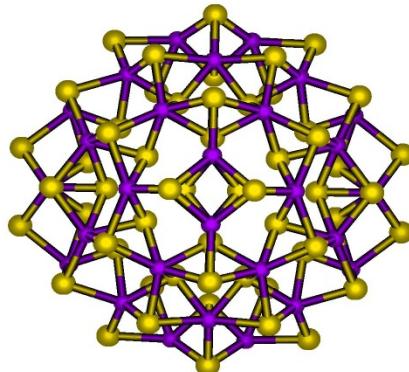


Seifert, G., Terrones, H., Terrones, M., Jungnickel, G., Frauenheim, T. Solid State Communications 114, 245-248 (2000). Seifert, G., Terrones, H., et al., PRL, Vol. 85, 146,(2000).

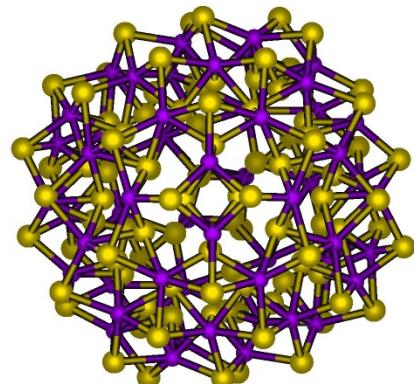
Octahedral Inorganic Fullerenes



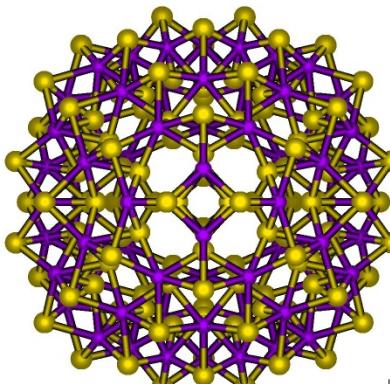
Mo₃₆S₇₂



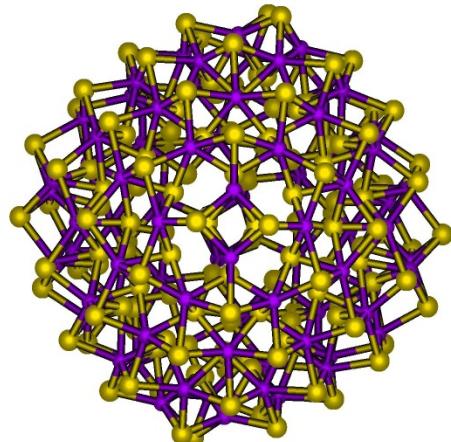
Mo₄₈S₉₆



Mo₅₂S₁₀₄

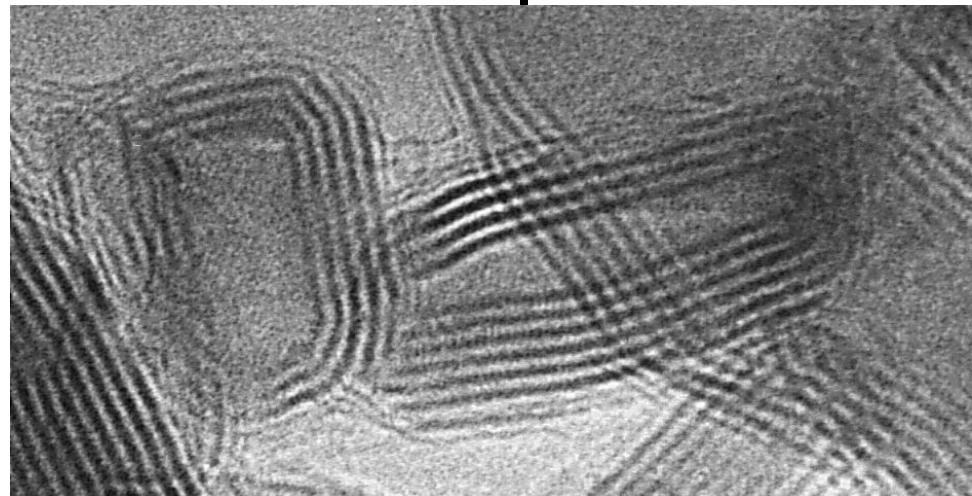


Mo₆₄S₁₂₈

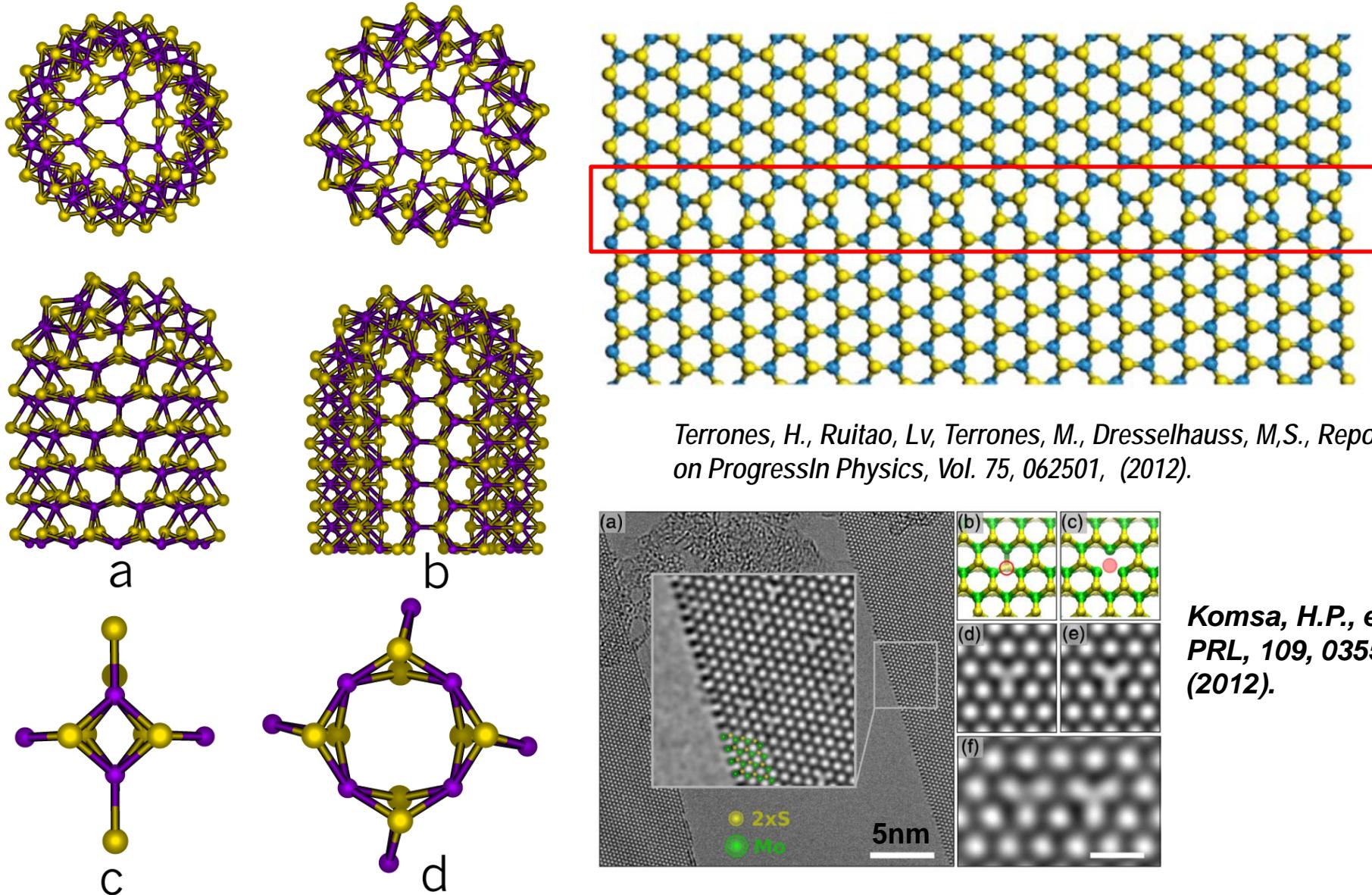


Mo₇₆S₁₅₂

WS₂ nanoparticles



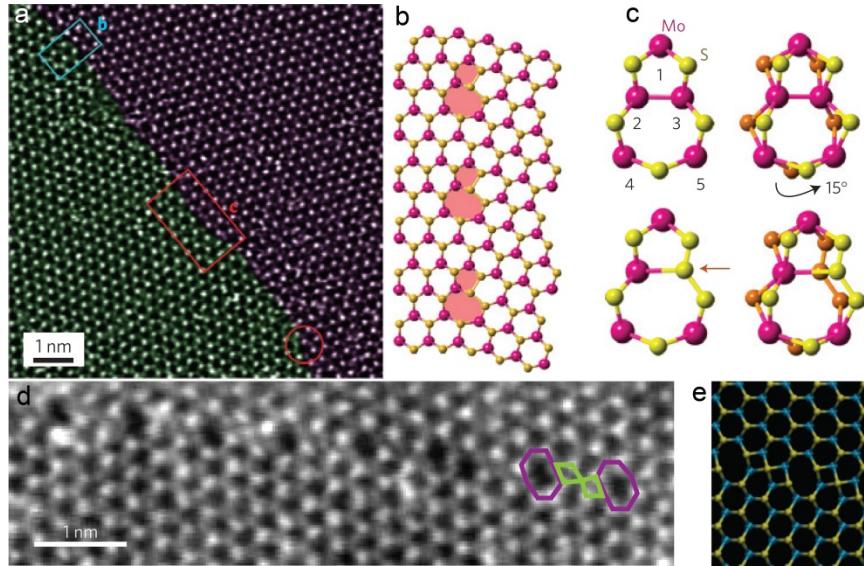
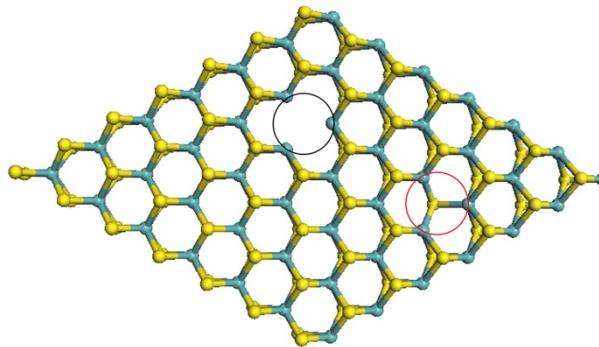
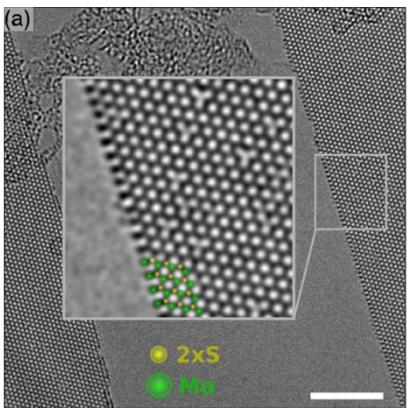
Topological defects and vacancies in TMD



Terrones, H., Ruitao, Lv, Terrones, M., Dresselhauss, M.S., Reports on Progress in Physics, Vol. 75, 062501, (2012).

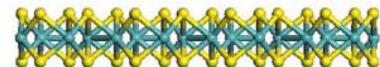
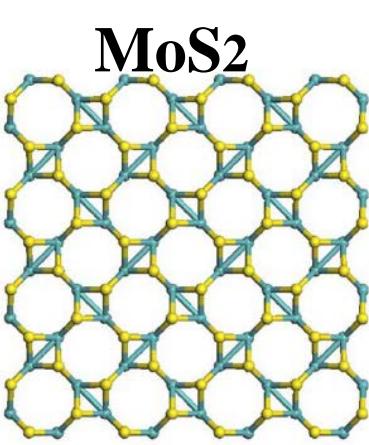
Komsa, H.P., et al.
PRL, 109, 035503
(2012).

Defects in monolayer TMDs

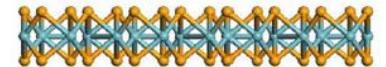
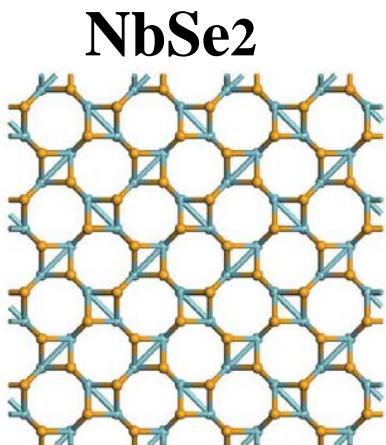


Point defects: vacancies, divacancies

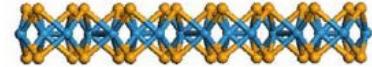
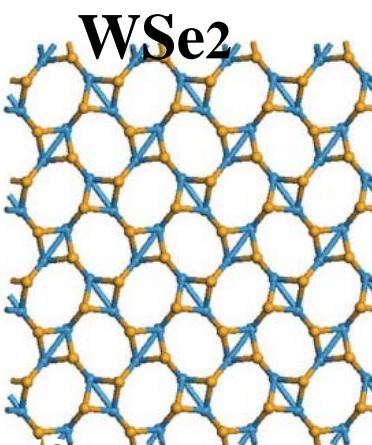
Komsa et al., PRL, Vol.109, art. 035503 (2012)



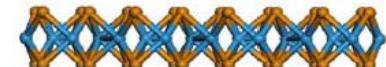
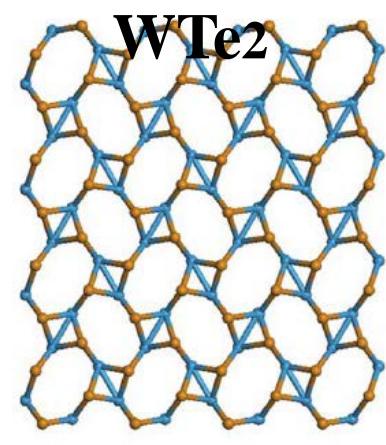
Semimetal



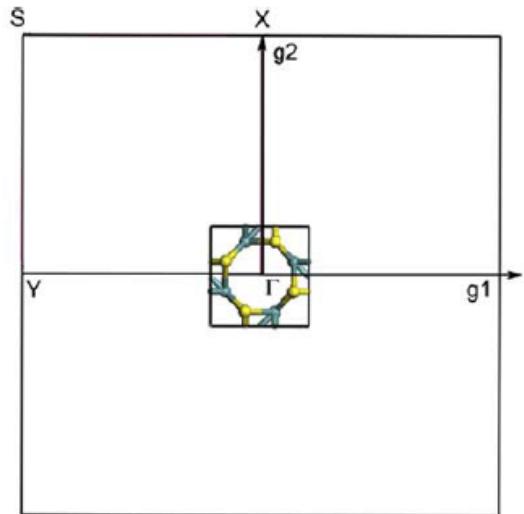
Semiconductor



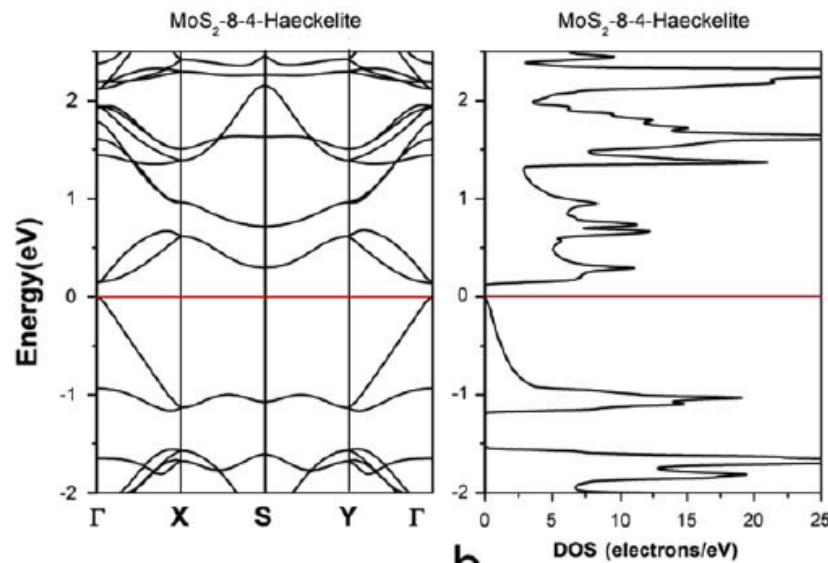
Semimetal



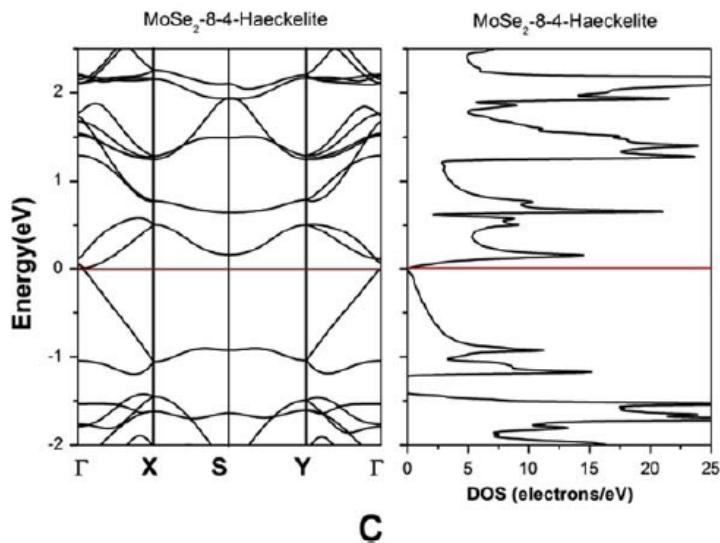
Semimetal



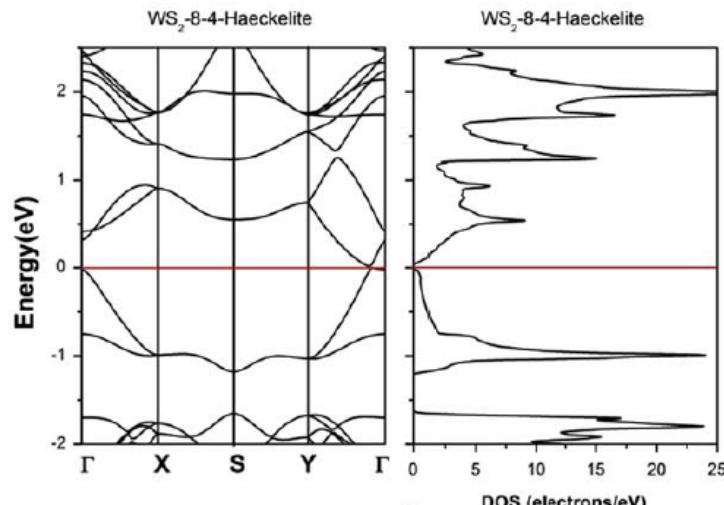
a



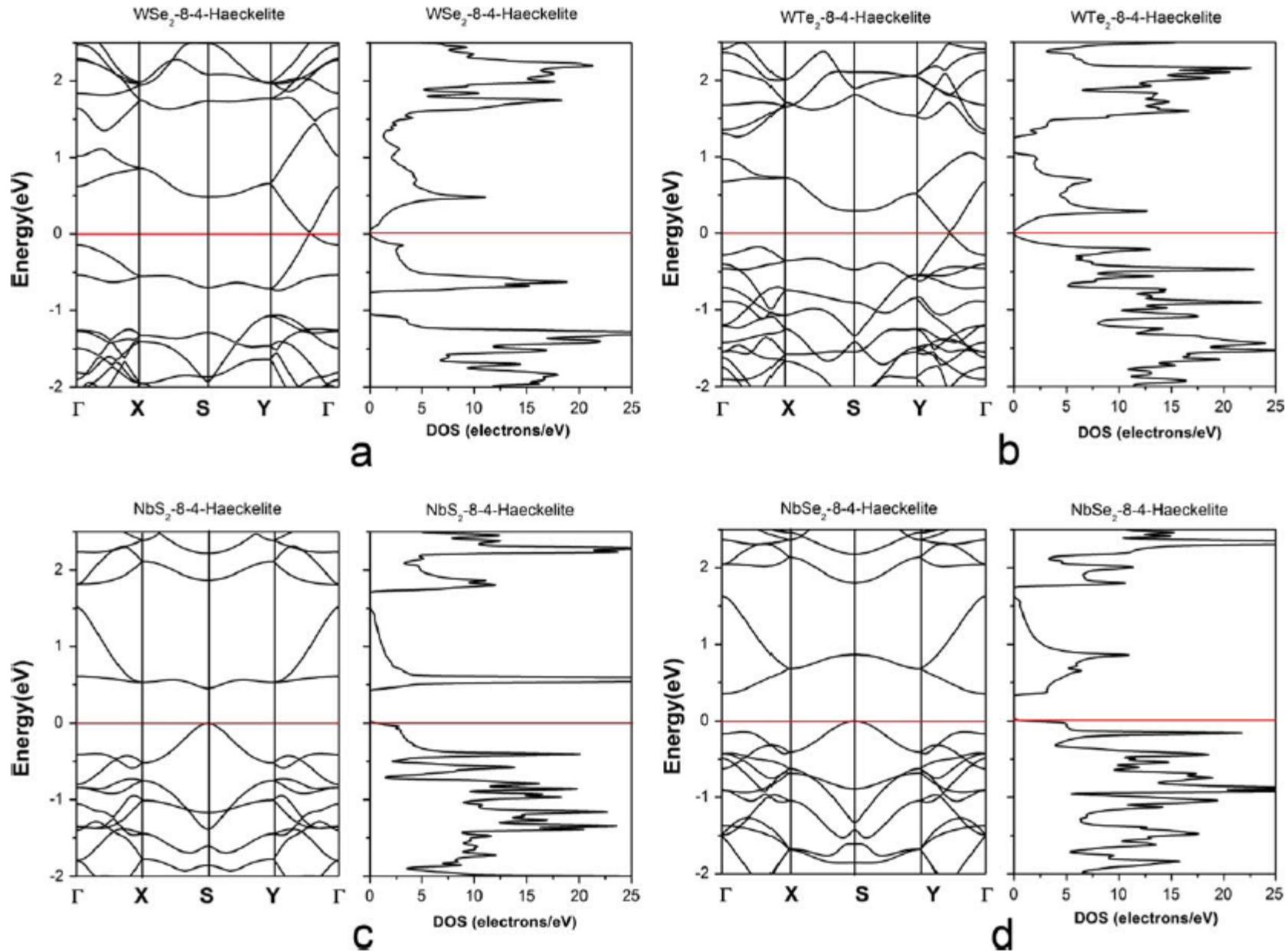
b



c



d



Monolayer MoS₂ by exfoliation

PRL 105, 136805 (2010)

PHYSICAL REVIEW LETTERS

week ending
24 SEPTEMBER 2010

Atomically Thin MoS₂: A New Direct-Gap Semiconductor

Kin Fai Mak,¹ Changgu Lee,² James Hone,³ Jie Shan,⁴ and Tony F. Heinz^{1,*}

NANO
LETTERS

pubs.acs.org/NanoLett

Emerging Photoluminescence in Monolayer MoS₂

Andrea Splendiani,^{†,‡} Liang Sun,[†] Yuanbo Zhang,[†] Tianshu Li,[§] Jonghwan Kim,[†] Chi-Yung Chim,[†] Giulia Galli,[§] and Feng Wang^{*,†,||}

Vol. 10,
1271,(2010).

NANO
LETTERS

LETTER

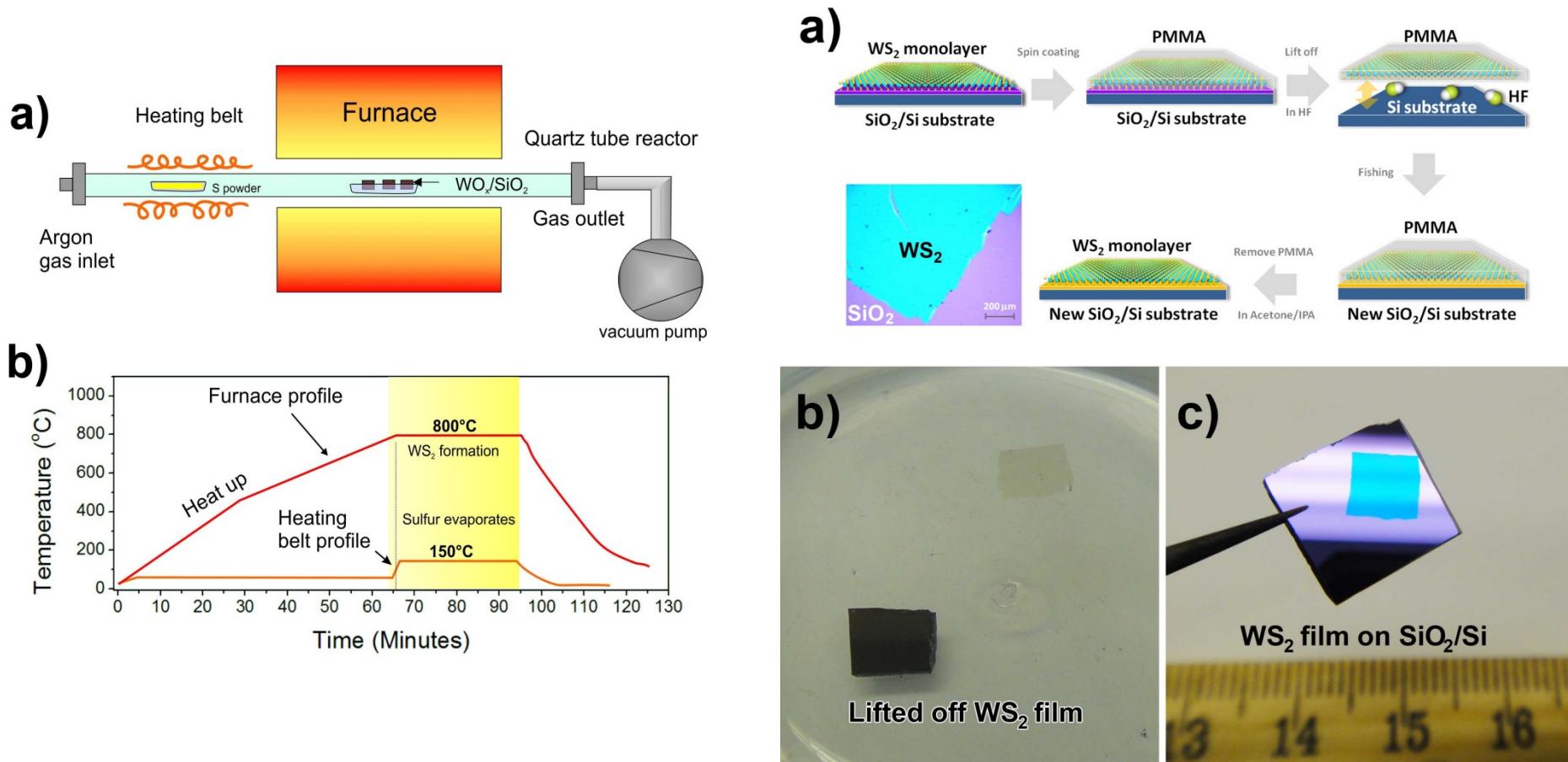
pubs.acs.org/NanoLett

Vol. 11,
5111,(2011).

Photoluminescence from Chemically Exfoliated MoS₂

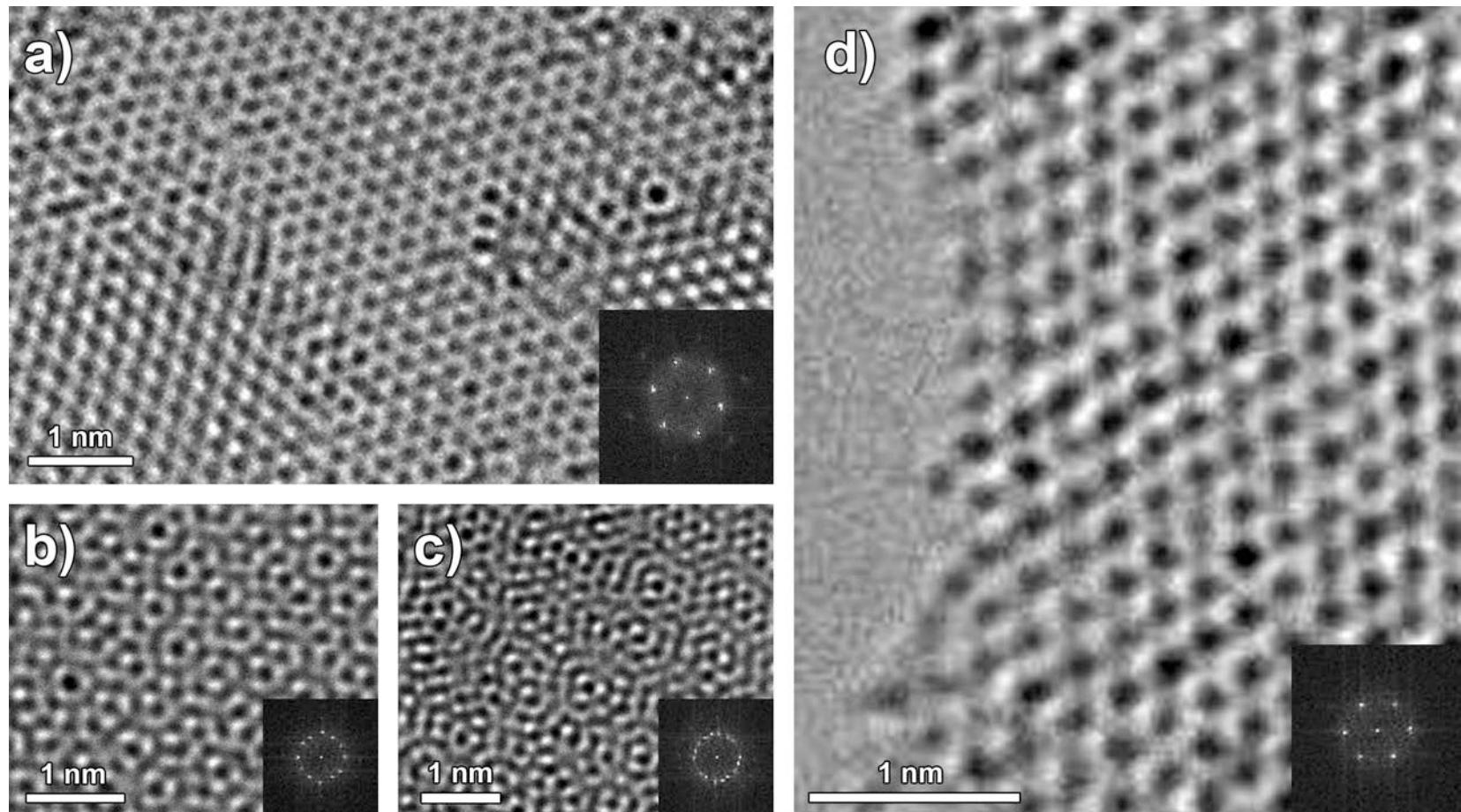
Goki Eda,^{*,†,‡,§} Hisato Yamaguchi,^{‡,§} Damien Voiry,[‡] Takeshi Fujita,^{§,||} Mingwei Chen,[§] and Manish Chhowalla[‡]

WS₂ synthesis by CVD



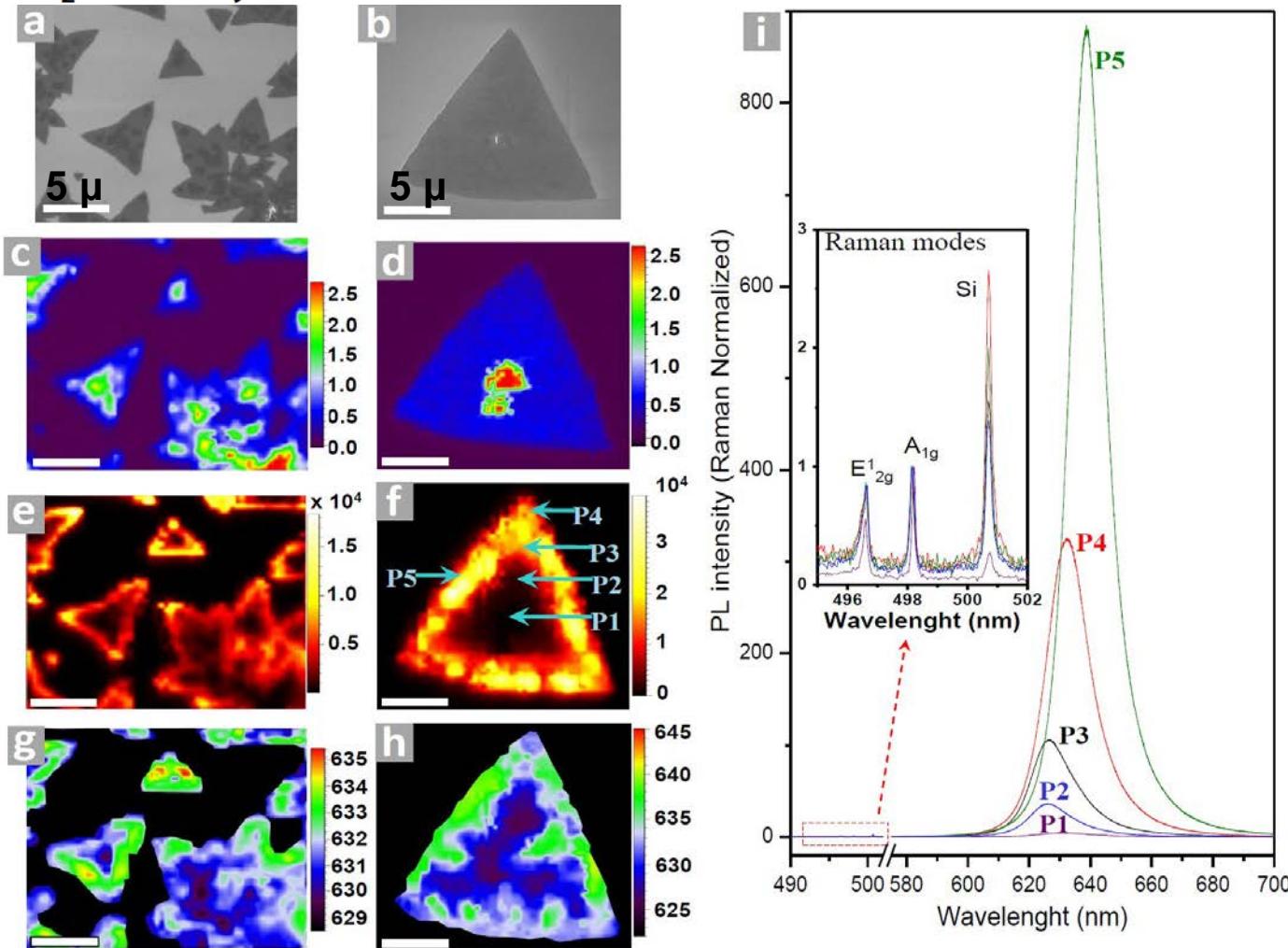
Elias, A.L., et al., ACS Nano, Vol. 7, 5235 (2013)

WS₂ Monolayer synthesis

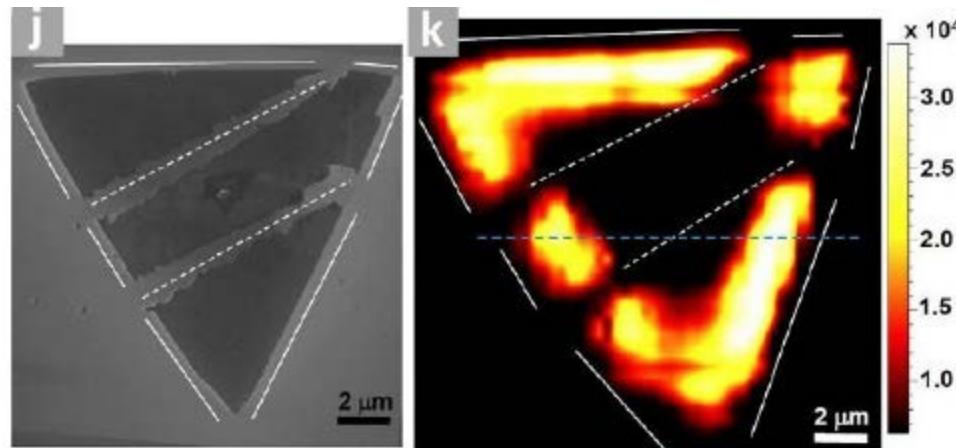


Elias, A.L., et al., ACS Nano, Vol. 7, 5235 (2013)

Extraordinary Room-Temperature Photoluminescence in Triangular WS₂ Monolayers

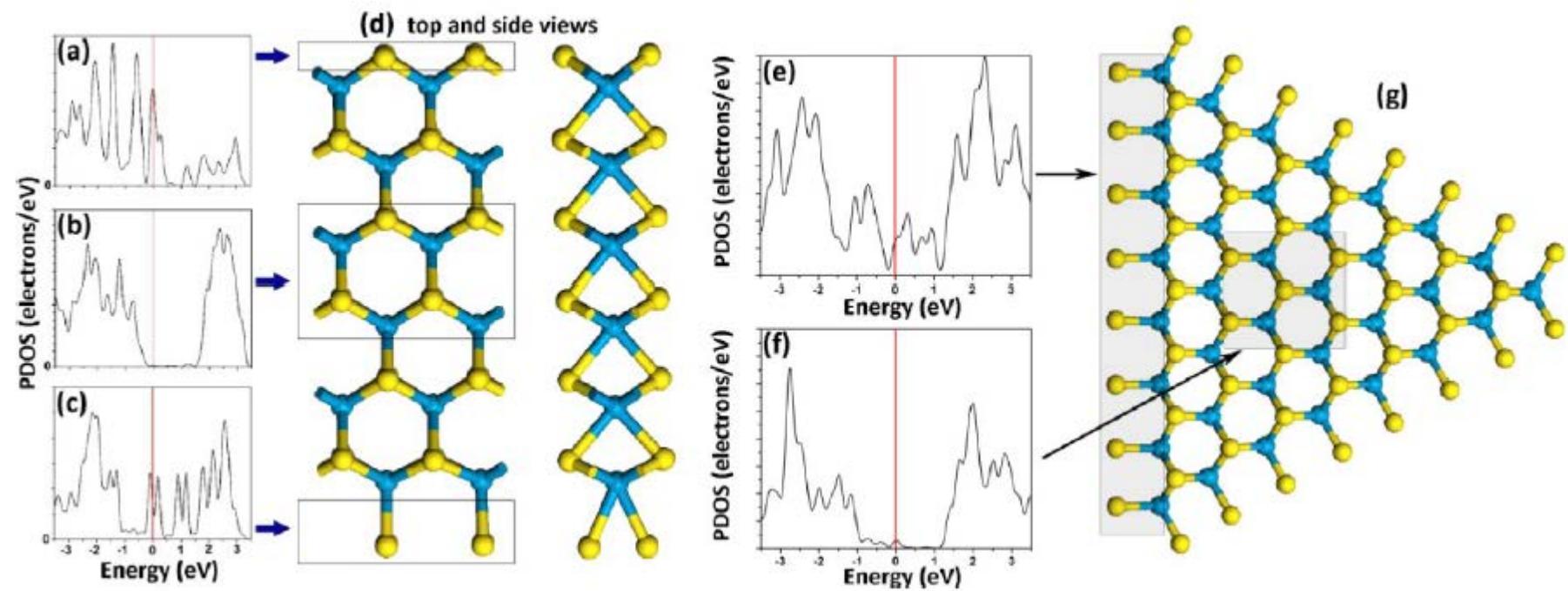


Edge behavior in WS₂ monolayer



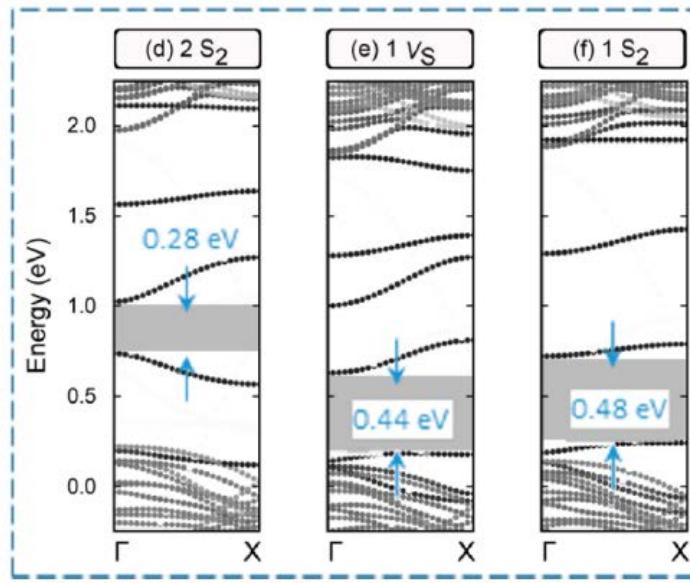
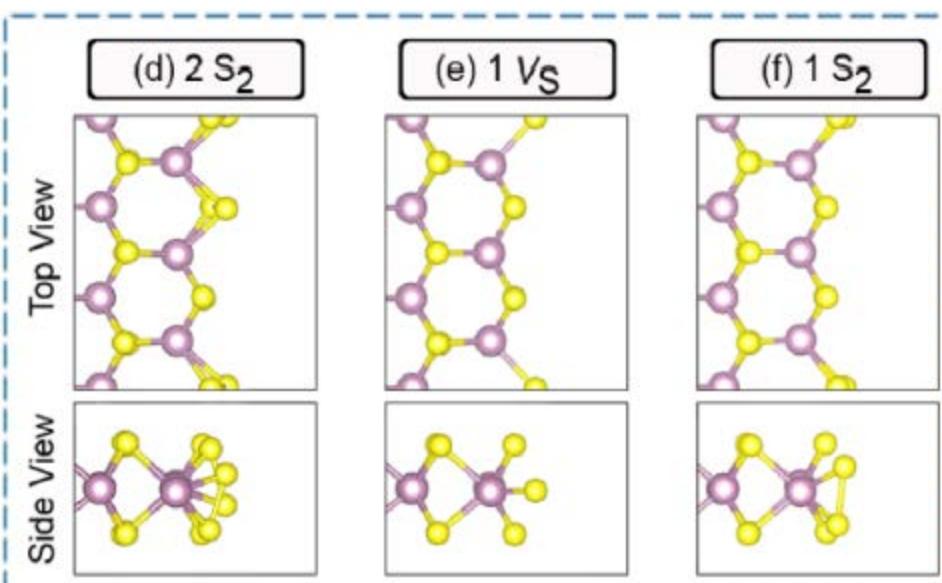
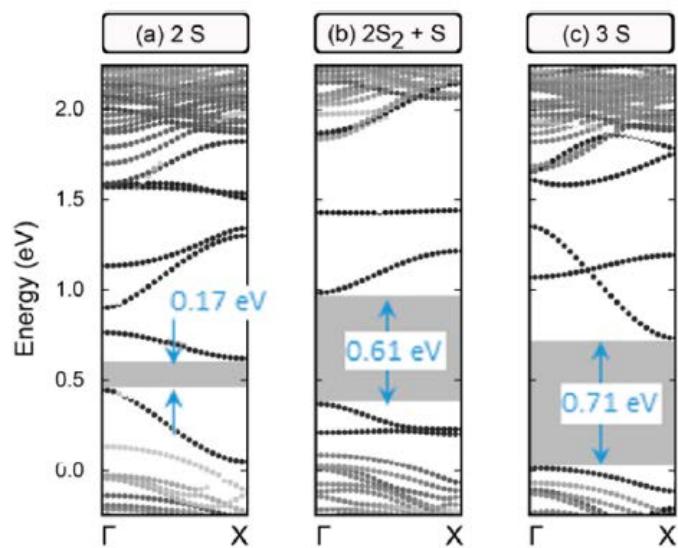
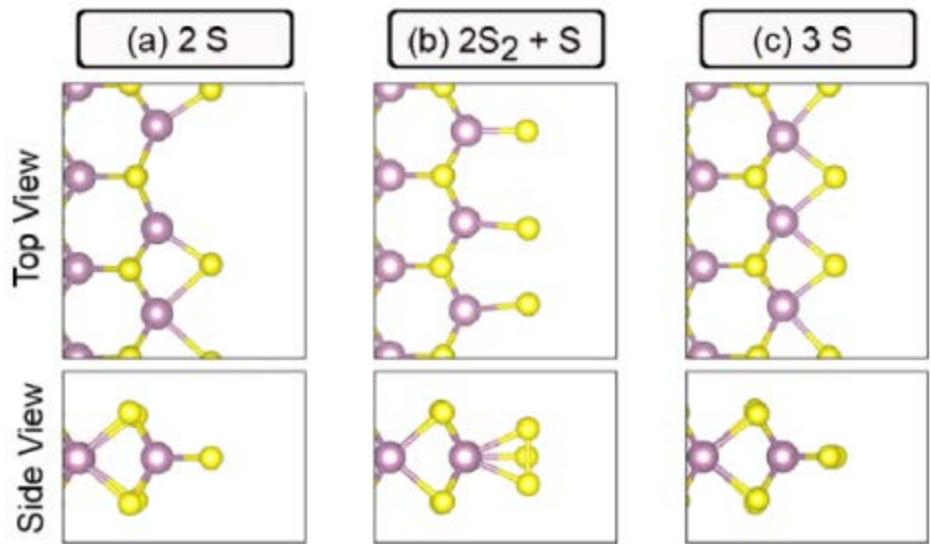
Gutierrez, H.R. et al., Nanoletters, Vol. 13, 3347 (2013)

Sulfur passivation DFT calculations

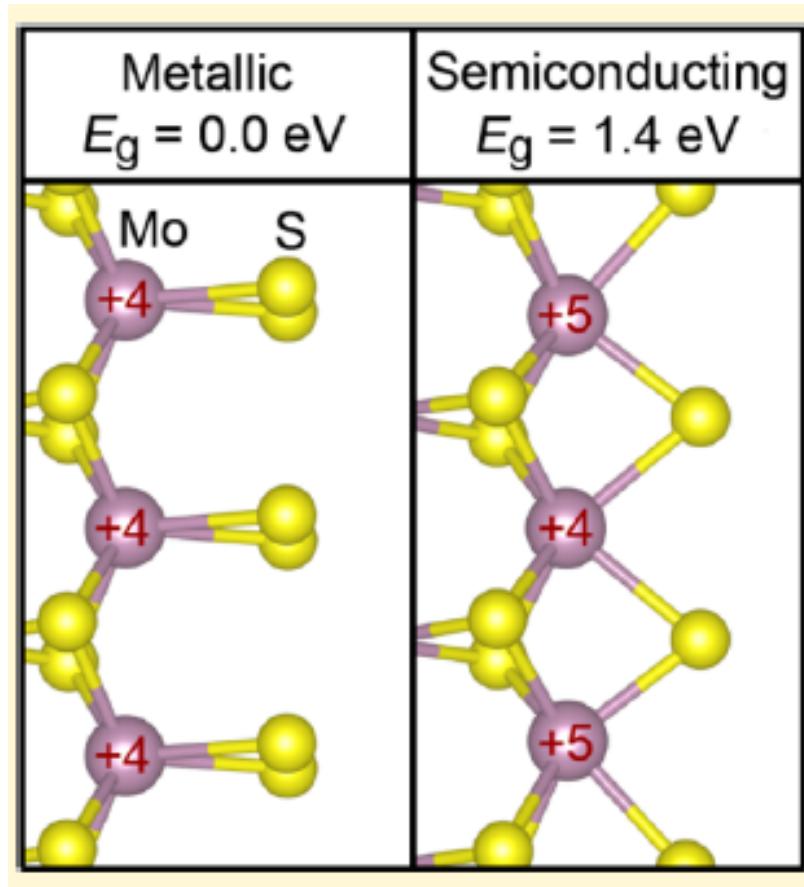


Metallic-like behavior at the edges

Gutierrez, H.R. et al., Nanoletters, Vol. 13, 3347 (2013)



Mo Valency change at the ribbon's edge

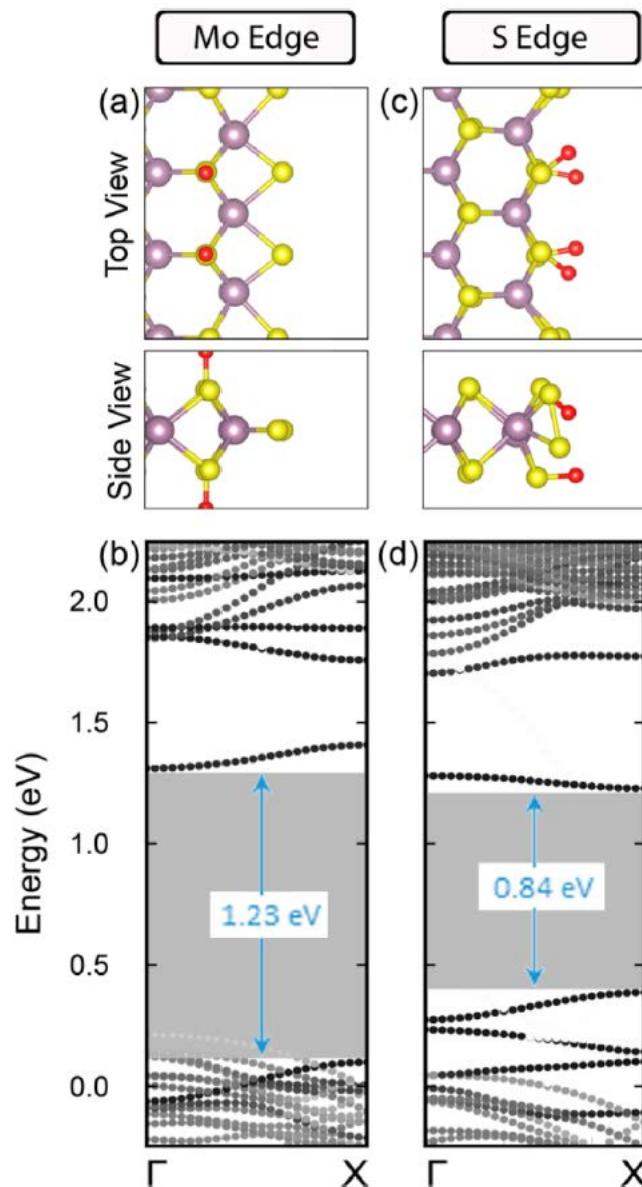


3S case

With HSE hybrid approximation the band gap is 1.4 eV

The band gap with GGA-PBE is 0.71 eV

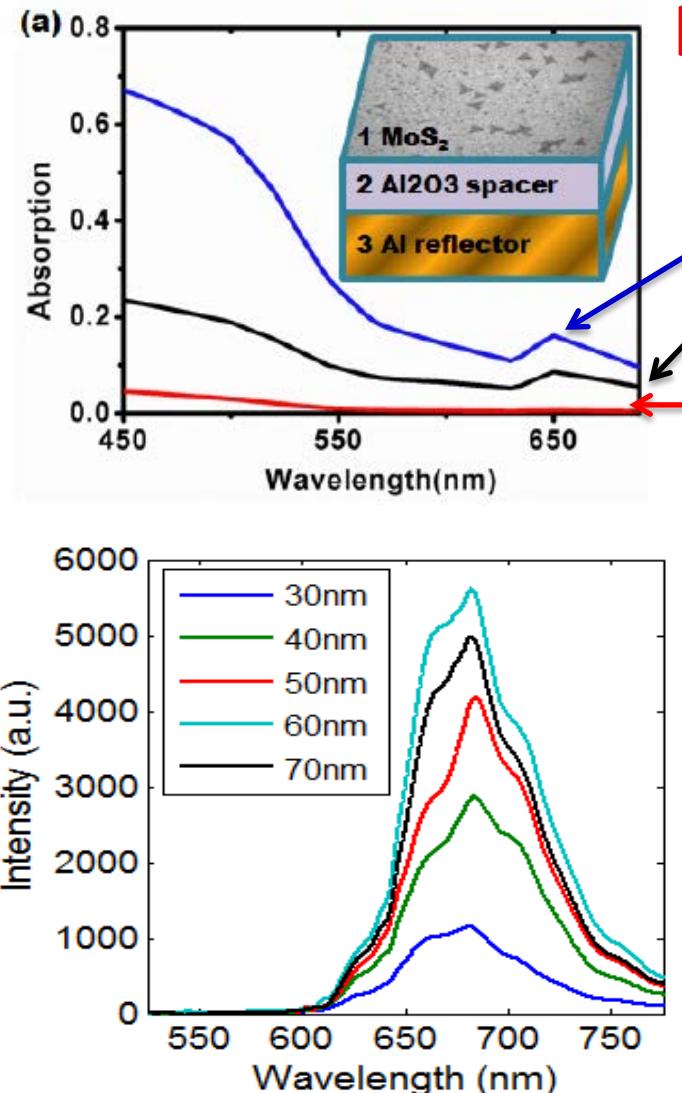
Role of Oxygen and Sulfur at the edges



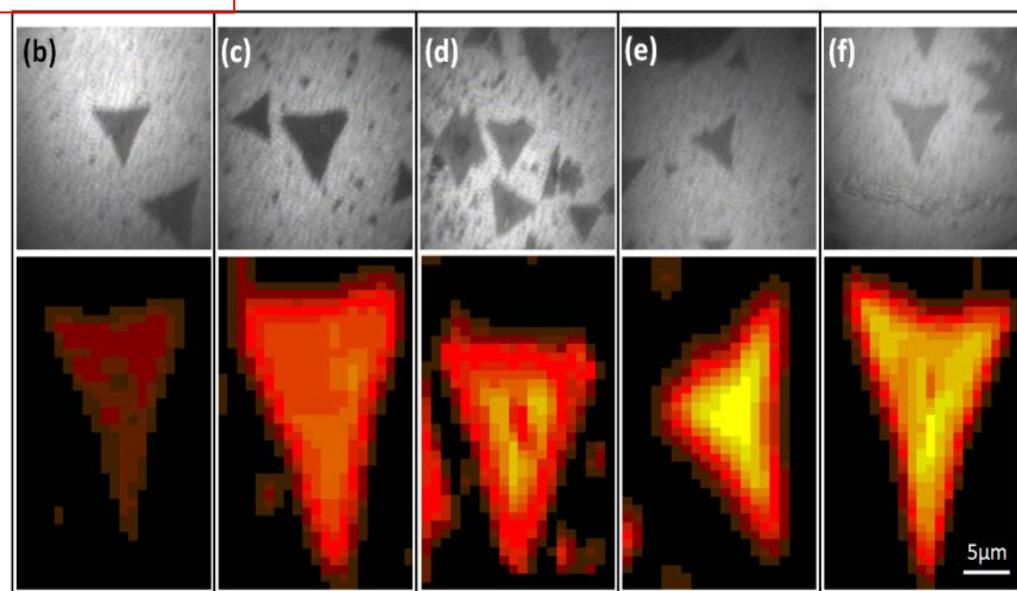
**With the HSE hybrid approximation
The gaps become more realistic
and increase**

1.23eV → 1.8eV (Mo Edge)
0.84eV → 1.6eV (S Edge)

PL of MoS₂ monolayers on different nanocavities



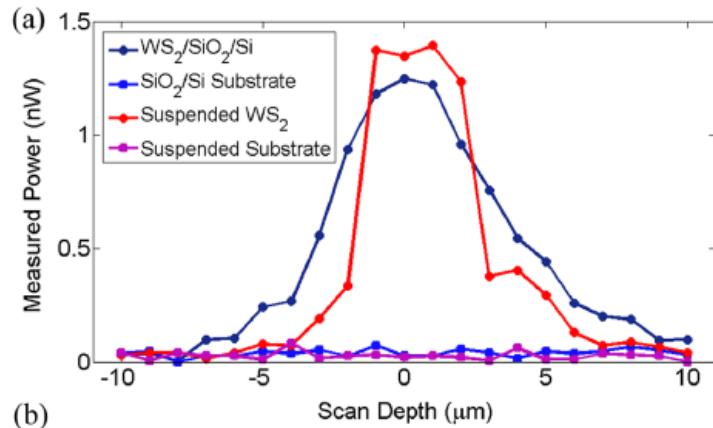
Janish, C. Et al., submitted



Planar nanocavities can enhance the light-matter interaction:

- Enhance the exclusive absorption of the 2D materials
- Modification of the spontaneous emission rate

Monolayer trigonal prismatic TMD exhibit no inversion symmetry and show second harmonic generation:



Janish, C., et al., Sci. Rep. 4 : 5530 | DOI:10.1038/srep05530;
Kumar, N et al., PRB, Vol. 87, 161403 (2013);

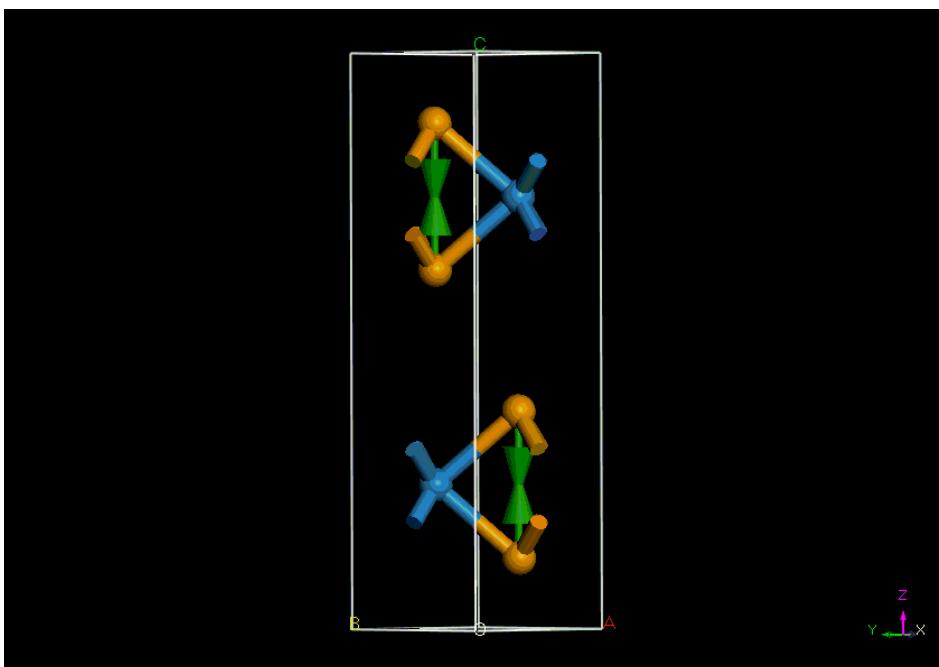


Electrical control of second-harmonic generation in a WSe₂ monolayer transistor

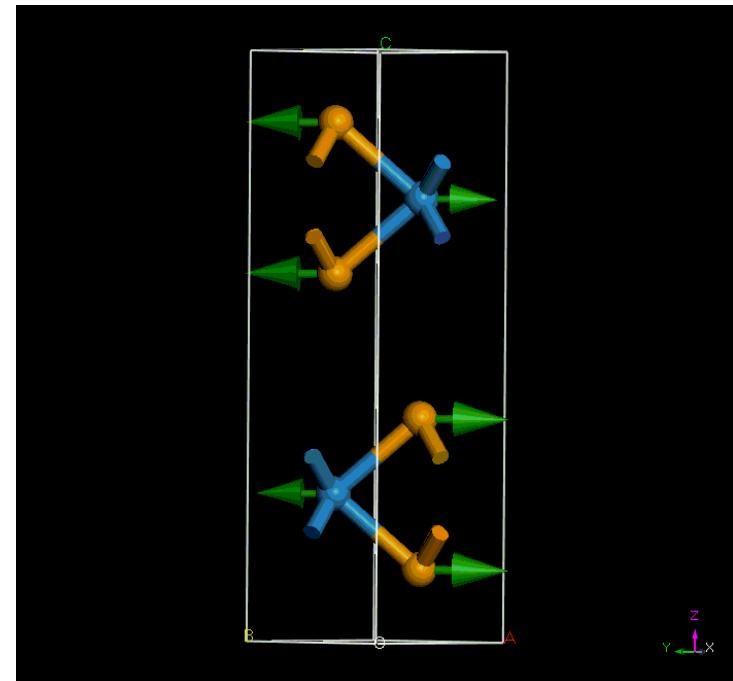
Kyle L. Seyler¹, John R. Schaibley¹, Pu Gong², Pasqual Rivera¹, Aaron M. Jones¹, Sanfeng Wu¹, Jiaqiang Yan^{3,4}, David G. Mandrus^{3,4,5}, Wang Yao² and Xiaodong Xu^{1,6*}

Raman Modes in Bulk TMDs

Trigonal prismatic semiconducting TMDs belong to the same space group P6₃/mmc(194; Nonsymmorphic; Schoenflies notation point group D_{6h})

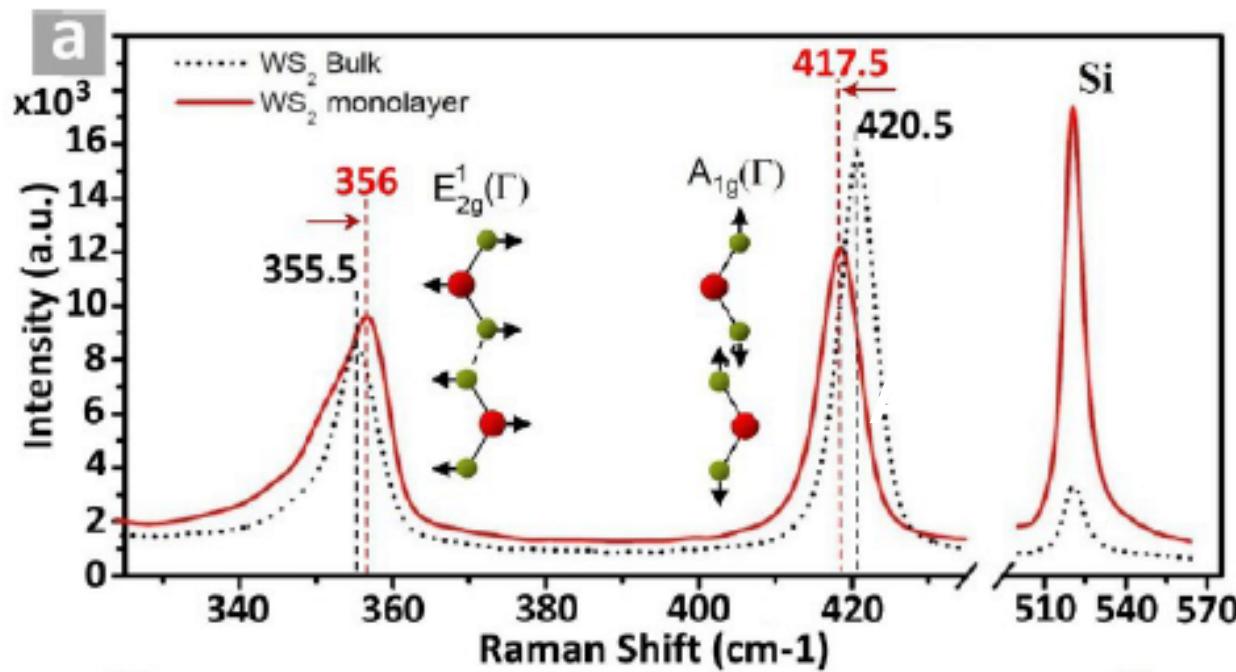
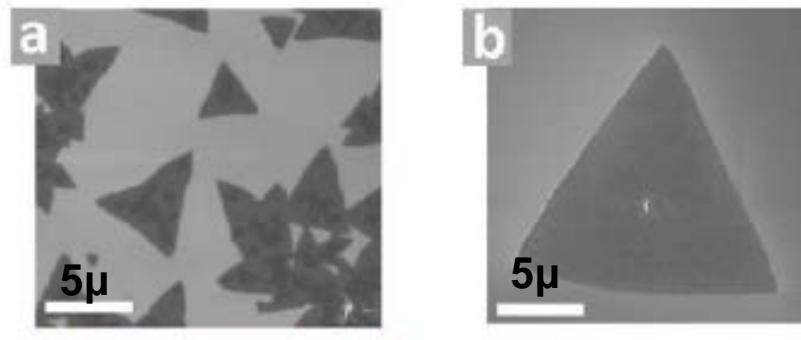


A_{1g}
Out of plane

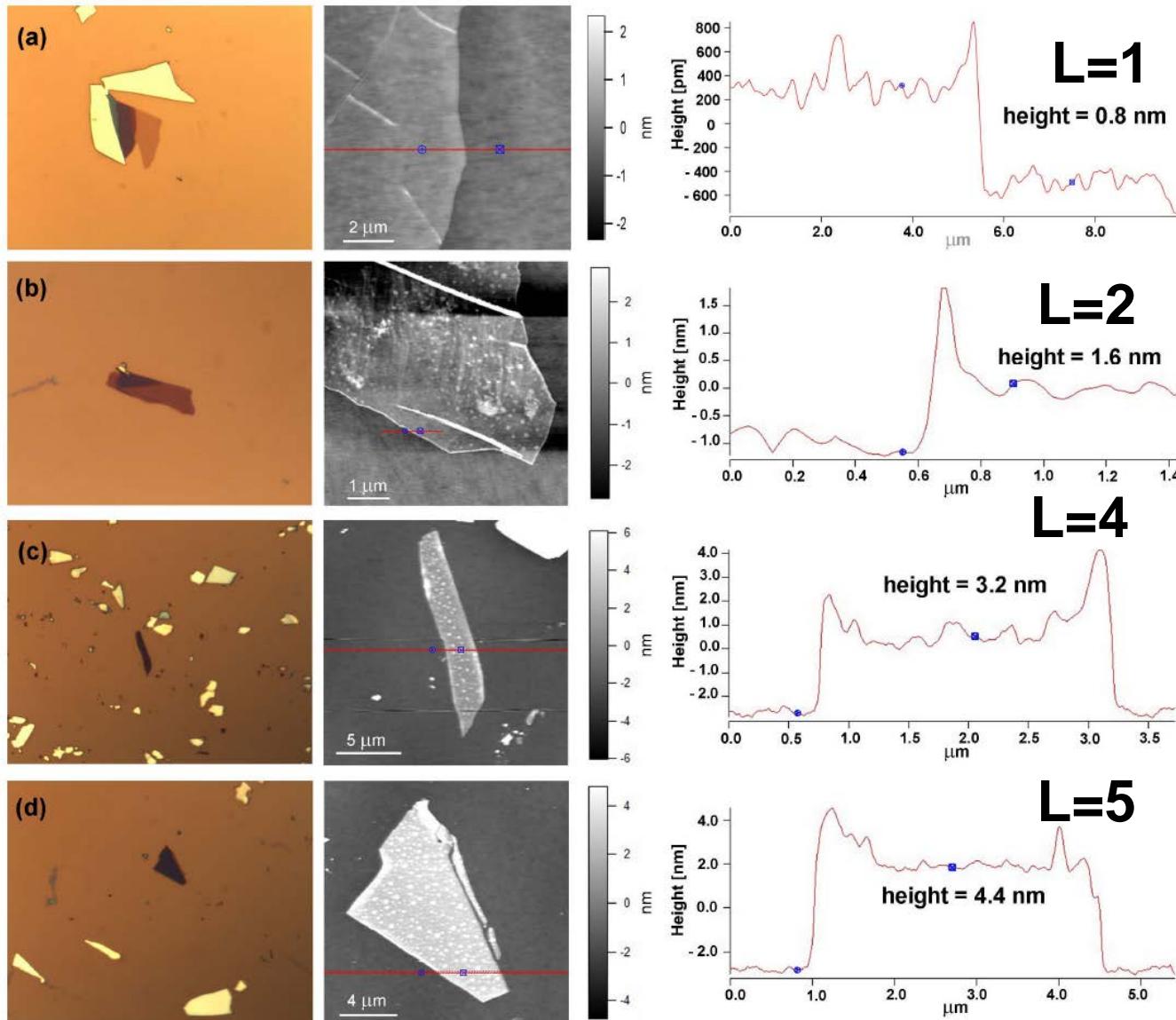


E_{2g}
in plane

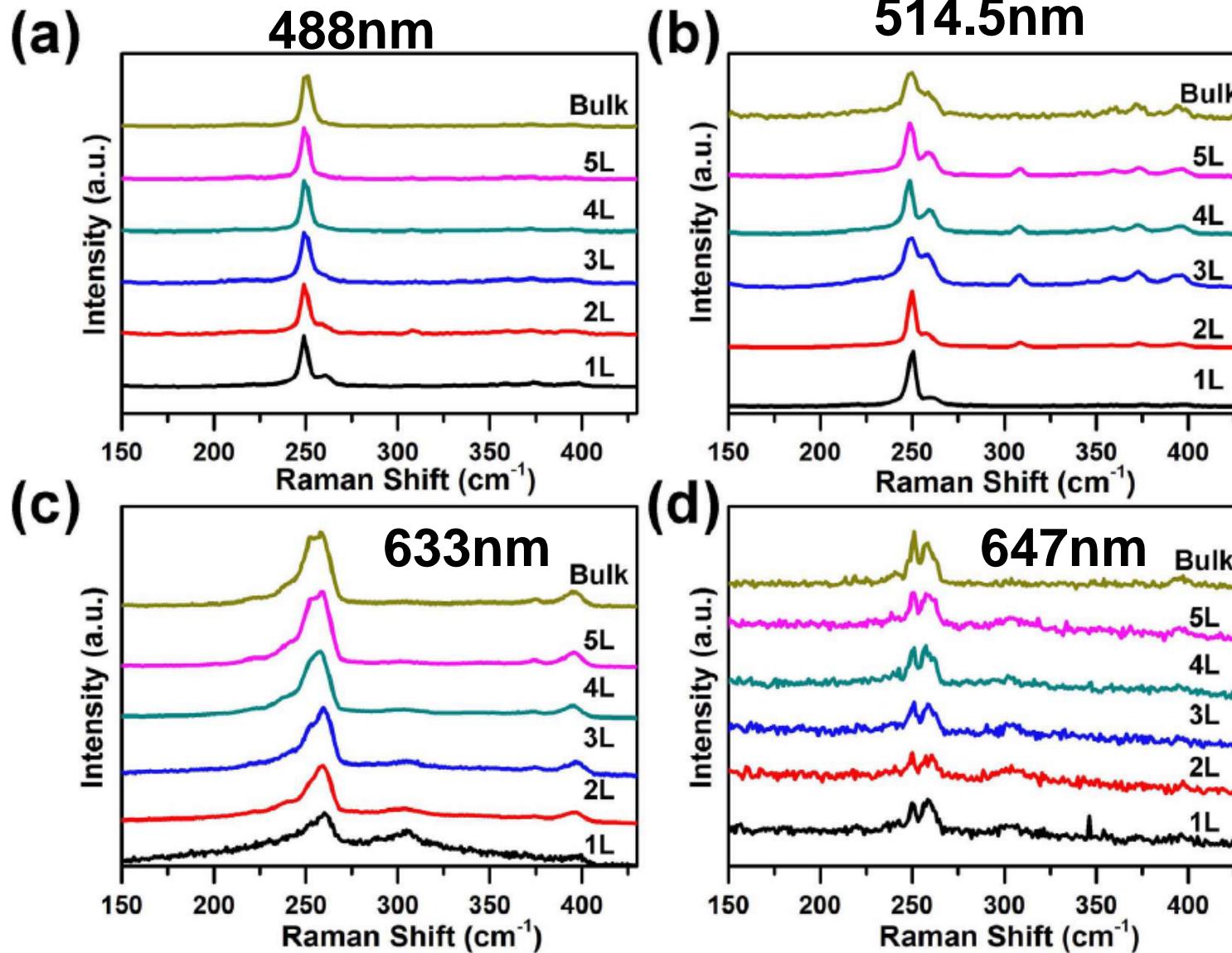
Raman Monolayer WS₂ (CVD)



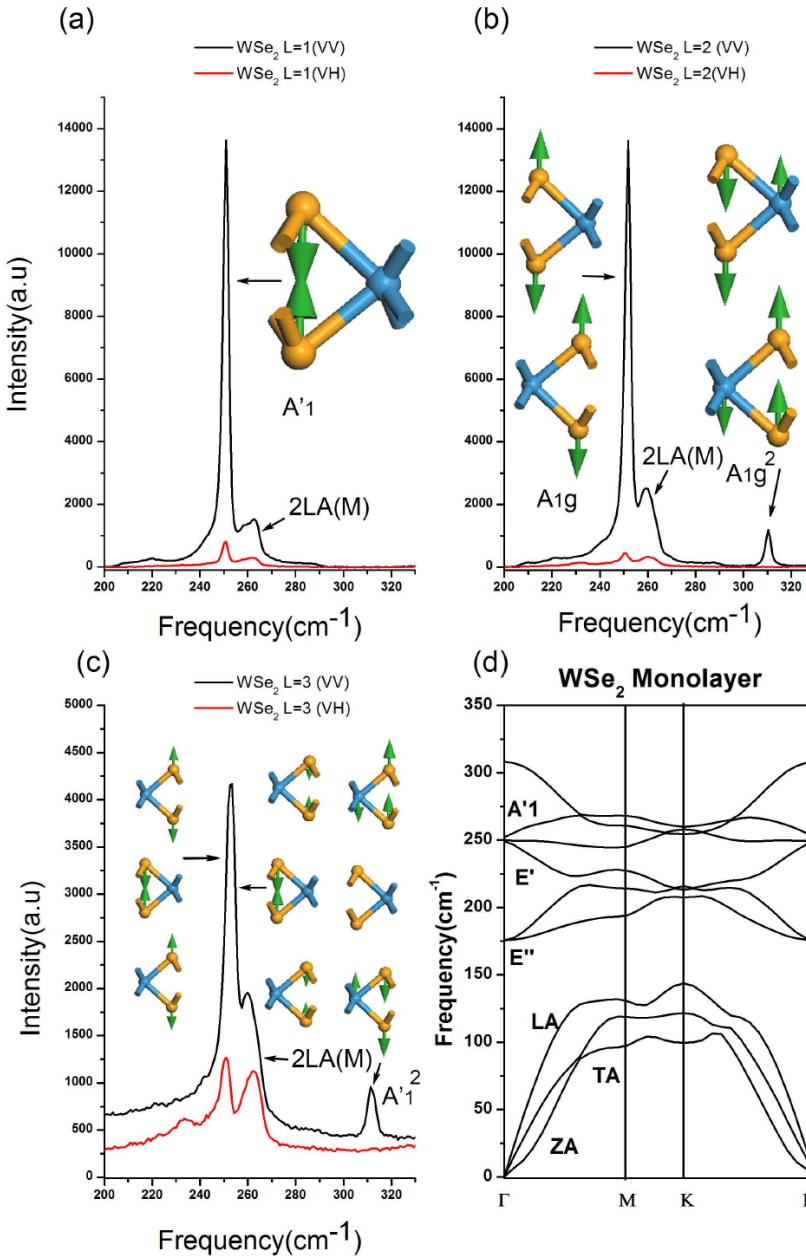
Layered WSe₂ (CVT) by Mechanical Exfoliation



Layered WSe₂ (CVT) by Mechanical Exfoliation



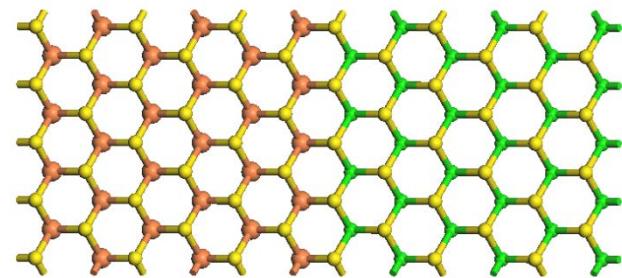
Layered WSe₂ (CVT) by Mechanical Exfoliation



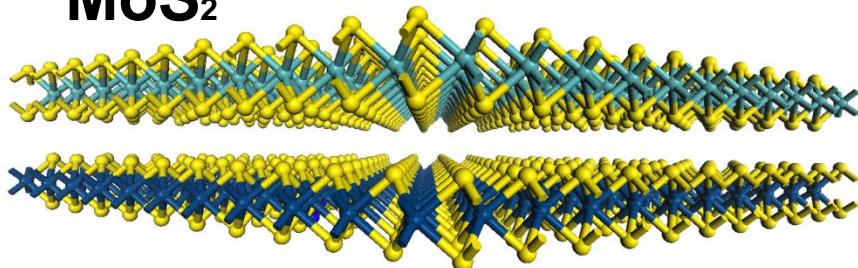
Density functional
perturbation theory
Using the code
CASTEP

Heterostructures of TMDs

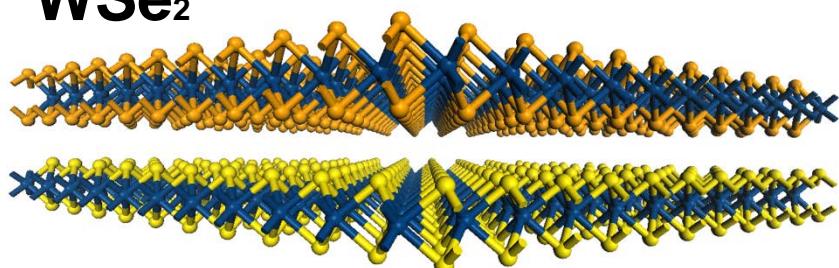
Can we mix layers or have different types of atoms in one layer? Yes



MoS₂

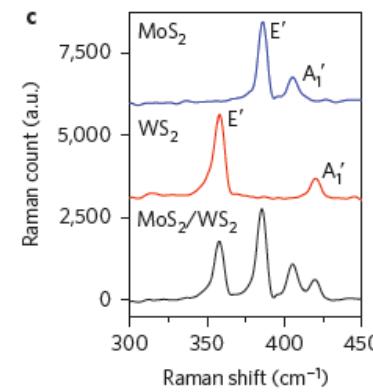
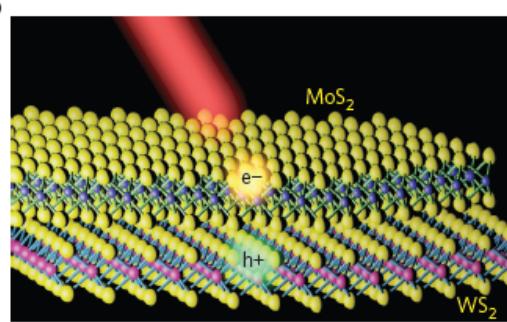
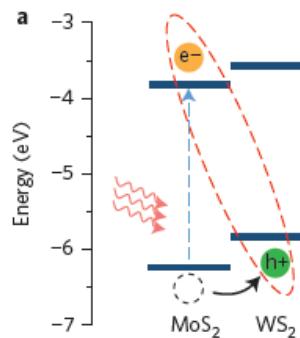


WSe₂



WS₂

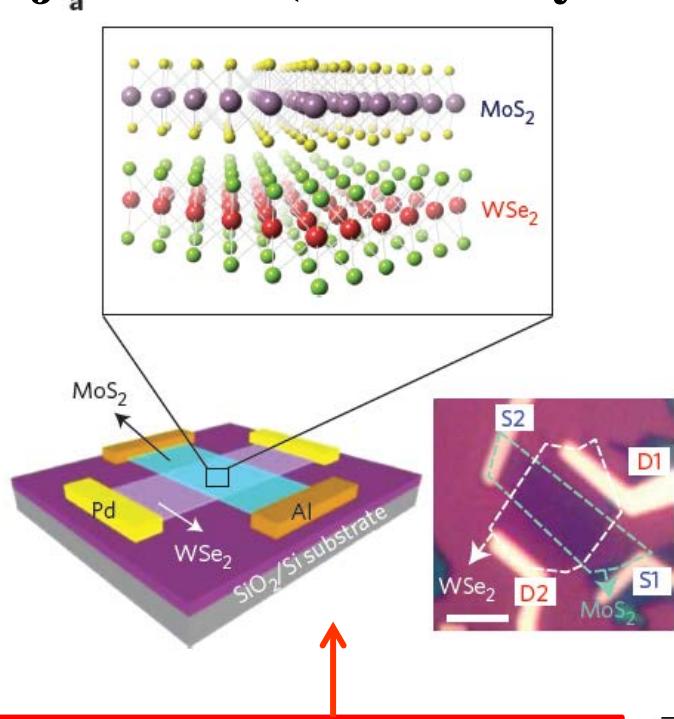
Terrones, H., et al., scientific Reports, Vol. 3, 1549 (2103)



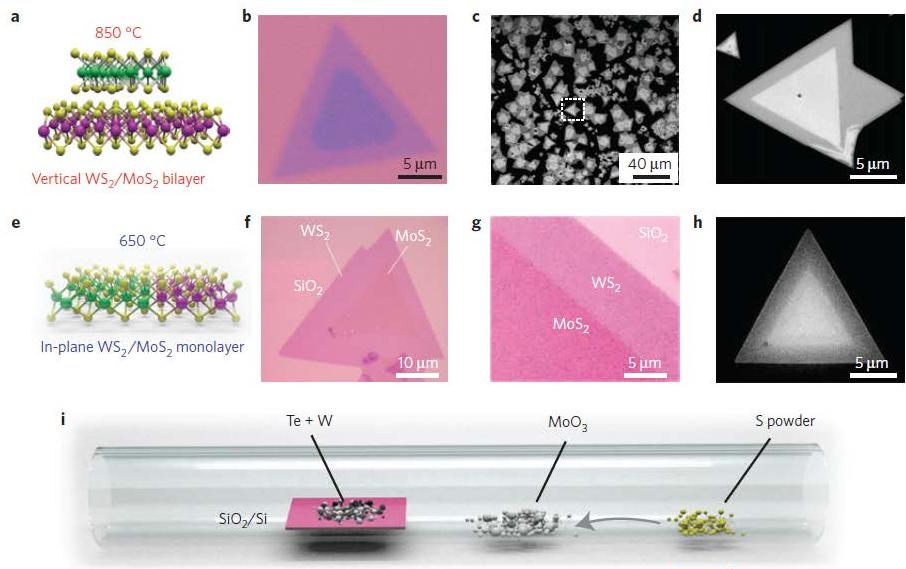
Ultra fast charge transfer 50×10^{-15} sec after optical excitation

Heterostructures of TMDs

p-n junction (atomically thin)



By mechanical exfoliation (scotch tape)
Lee, C-H., et al., Nature nanotechnology, Vol.10 DOI: 10.1038/NNANO.2014.150 (2104)

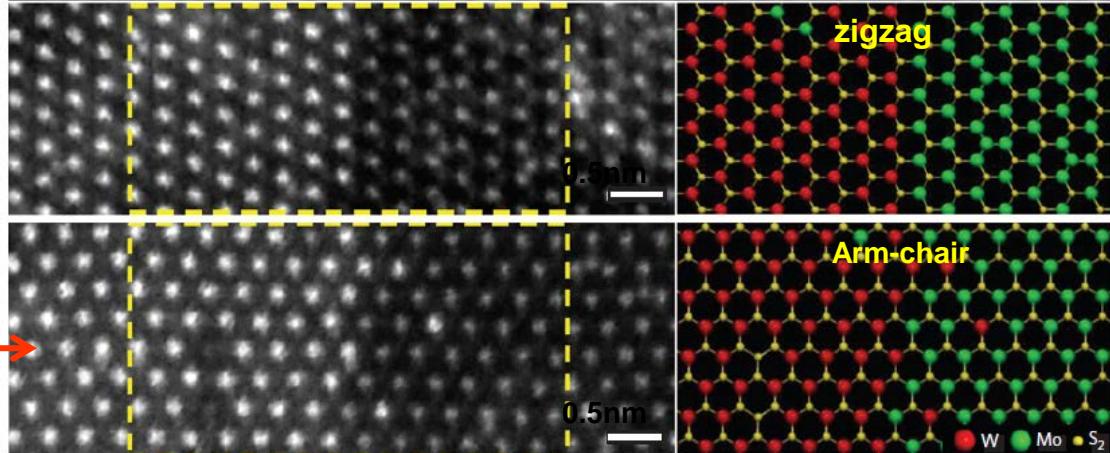


By CVD

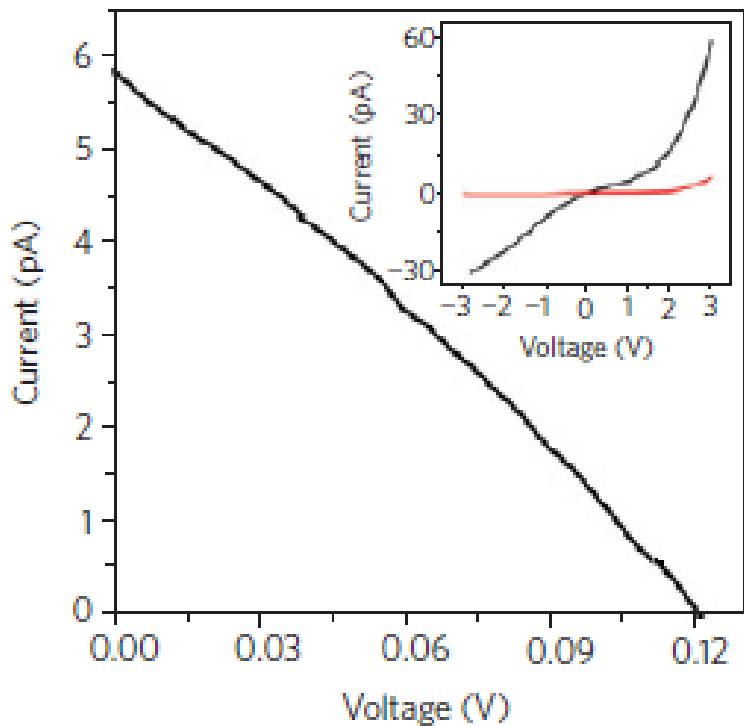
Gong, J., et al, Nature Materials, PUBLISHED ONLINE:
28 SEPTEMBER 2014 | DOI: 10.1038/NMAT4091

Atomic resolution z-contrast STEM

Gong, J., et al, Nature Materials, PUBLISHED ONLINE:
28 SEPTEMBER 2014 | DOI: 10.1038/NMAT4091

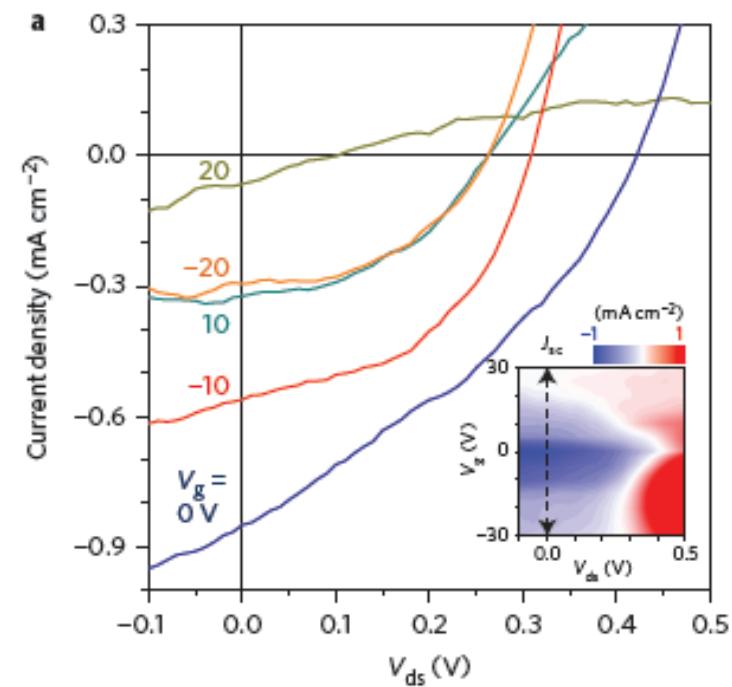


Heterostructures of TMDs



Photovoltaic effect of the in plane heterojunction (MoS₂/WS₂)
open-loop voltage of 0.12 V and close-loop current of
5.7 pA

Gong, J., et al, Nature Materials, PUBLISHED
ONLINE:28 SEPTEMBER 2014 | DOI:
10.1038/NMAT4091



Photovoltaic effect in MoS₂/WSe₂ bilayer heterojunction

Lee, C-H., et al., Nature nanotechnology,
Vol.10 DOI: 10.1038/NNANO.2014.150 (2104)

Challenges:

- Mass production of single layers
- Control of defects, doping and grain boundaries
- Control of stacking
- Contacts with metals or other TMDs

Acknowledgements:

**NSF (EFRI-1433311), U.S. Army Research Office MURI
grant W911NF-11-1-0362, Penn State Center for
Nanoscale Science Seed grant on 2-D Layered Materials
(DMR-0820404).**

Thank you